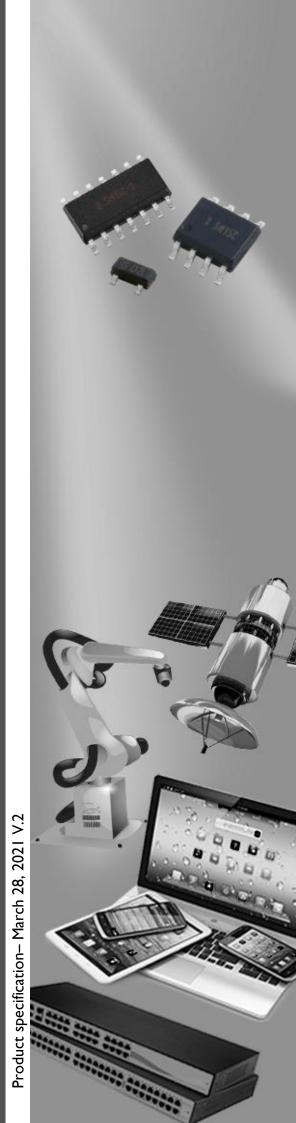


# **DATA SHEET**

ELECTROSTATIC DISCHARGE PROTECTION DEVICES INDUSTRIAL / CONSUMER UDD32CXXL01 series

RoHS compliant & Halogen free





### Electrostatic Discharged Protection Devices (ESD) Data Sheet

### **Description**

The series are an ultra low capacitance TVS array designed to protect high speed data interfaces. This series has been specifically designed to protect sensitive components which are connected to data an trans--mission lines from overvoltage caused by electrostatic discharge (ESD), cable discharge events (CDE) and lightning.

The unique design incorporates surge rated, low capacitance steering diodes and a TVS diode in a single package. During transient conditions, the steering diodes direct the transient current to ground. The internal TVS diode clamps the transient voltage to a safe level. The ultra low capacitance array configuration allows the user to protect up to the high speed data lines. These devices are in a signal package, RoHS/WEEE compliant, SOD-323 package. It measures 2.5×1.25×1.0mm.

The series devices may be used to meet the immunity requirements of IEC61000-4-2 (ESD), IEC61000-4-4 (EFT) and IEC61000-4-5 (Surge).



Contact: ±30kV Air: ±30kV



### **Features**

- IEC61000-4-2 ESD 30KV Air, 30KV contact compliance ESD 15KV Air, 8KV contact compliance for UDD32C36L01
- SOD-323 surface mount package
- Protects one I/O line
- Working voltage: 3V, 5V, 8V, 12V, 15V, 24V, 36V
- Low leakage current
- Low operating and clamping voltages
- Solid-state silicon avalanche technology
- Lead Free/RoHS compliant
- Solder reflow temperature: Pure Tin-Sn, 260~270°C
- Flammability rating UL 94V-0
- Meets MSL level 1, per J-STD-020

# Pin Configuration

### **Applications**

- USB 2.0 and USB 3.0 interface
- 10/100/1000 Ethernet
- Personal digital assistants (PDA)
- Serial ATA protection
- Digital visual interface (DVI)

- Wireless system devices
- Handhelds and notebooks
- Digital cameras
- RF interface



### **Maximum Ratings**

Rating	Symbol	Value	Unit
Peak pulse power (tp=8/20µs waveform)	P <sub>PP</sub>	350	W
ESD voltage (Contact discharge)	V	±30	kV
ESD voltage (Air discharge)	$V_{ESD}$	±30	KV
Storage & operating temperature range	T <sub>STG</sub> ,T <sub>J</sub>	-55~+150	$^{\circ}$

### Electrical Characteristics (T<sub>J</sub>=25°C)

UDD32C03L01 (Marking: AC)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Reverse stand-off voltage	$V_{RWM}$				3.3	V
Reverse breakdown voltage	$V_{BR}$	I <sub>BR</sub> =1mA	4			V
Reverse leakage current	I <sub>R</sub>	V <sub>R</sub> =3.3V			5	μΑ
Clamping voltage (tp=8/20µs)	V <sub>C</sub>	I <sub>PP</sub> =1A			7	V
Clamping voltage (tp=8/20µs)	Vc	I <sub>PP</sub> =5A			15	V
Peak Pulse Current (tp=8/20µs)	I <sub>PP</sub>				19	Α
Off state junction capacitance	CJ	0Vdc,f=1MHz		0.8		pF

UDD32C05L01 (Marking: BC)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Reverse stand-off voltage	$V_{RWM}$				5	V
Reverse breakdown voltage	$V_{BR}$	I <sub>BR</sub> =1mA	6			V
Reverse leakage current	I <sub>R</sub>	V <sub>R</sub> =5V			5	μΑ
Clamping voltage (tp=8/20µs)	Vc	I <sub>PP</sub> =1A			9.8	V
Clamping voltage (tp=8/20µs)	V <sub>C</sub>	I <sub>PP</sub> =5A			18.3	V
Peak Pulse Current (tp=8/20µs)	I <sub>PP</sub>				17	Α
Off state junction capacitance	CJ	0Vdc,f=1MHz		0.8		pF

UDD32C08L01(Marking: BC.)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Reverse stand-off voltage	$V_{RWM}$				8	V
Reverse breakdown voltage	$V_{BR}$	I <sub>BR</sub> =1mA	8.5			V
Reverse leakage current	I <sub>R</sub>	V <sub>R</sub> =8V			1	μA
Clamping voltage (tp=8/20µs)	Vc	I <sub>PP</sub> =1A			13	V
Clamping voltage (tp=8/20µs)	Vc	I <sub>PP</sub> =10A			24	V
Peak Pulse Current (tp=8/20µs)	I <sub>PP</sub>				17	Α
Off state junction capacitance	Сл	0Vdc,f=1MHz		1		pF

### Electrostatic Discharge Protection Devices | UDD32CXXL01

UDD32C12L01 (Marking: DC)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Reverse stand-off voltage	$V_{RWM}$				12	>
Reverse breakdown voltage	$V_{BR}$	I <sub>BR</sub> =1mA	13.3			V
Reverse leakage current	I <sub>R</sub>	V <sub>R</sub> =12V			1	μA
Clamping voltage (tp=8/20µs)	Vc	I <sub>PP</sub> =1A			19	V
Clamping voltage (tp=8/20µs)	Vc	I <sub>PP</sub> =5A			28.6	V
Peak Pulse Current (tp=8/20µs)	I <sub>PP</sub>				7	Α
Off state junction capacitance	Сл	0Vdc,f=1MHz		0.8		pF

UDD32C15L01 (Marking: EC)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Reverse stand-off voltage	$V_{RWM}$				15	V
Reverse breakdown voltage	$V_{BR}$	I <sub>BR</sub> =1mA	16.7			V
Reverse leakage current	$I_R$	V <sub>R</sub> =15V			1	μA
Clamping voltage (tp=8/20µs)	Vc	I <sub>PP</sub> =1A			24	V
Clamping voltage (tp=8/20µs)	Vc	I <sub>PP</sub> =5A			35	V
Peak Pulse Current (tp=8/20µs)	I <sub>PP</sub>				6	Α
Off state junction capacitance	CJ	0Vdc,f=1MHz		0.8		pF

UDD32C24L01 (Marking: HC)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Reverse stand-off voltage	$V_{RWM}$				24	V
Reverse breakdown voltage	$V_{BR}$	I <sub>BR</sub> =1mA	26.7			V
Reverse leakage current	I <sub>R</sub>	V <sub>R</sub> =24V			1	μA
Clamping voltage (tp=8/20µs)	Vc	I <sub>PP</sub> =1A			43	V
Clamping voltage (tp=8/20µs)	Vc	I <sub>PP</sub> =5A			56	V
Peak Pulse Current (tp=8/20µs)	I <sub>PP</sub>				6	Α
Off state junction capacitance	CJ	0Vdc,f=1MHz		0.8		pF

UDD32C36L01 (Marking: KC)

### \_\_\_\_\_

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Reverse stand-off voltage	$V_{RWM}$				36	V
Reverse breakdown voltage	$V_{BR}$	I <sub>BR</sub> =1mA	40			V
Reverse leakage current	I <sub>R</sub>	V <sub>R</sub> =36V			1	μA
Clamping voltage (tp=8/20µs)	Vc	I <sub>PP</sub> =1A			70	V
Clamping voltage (tp=8/20µs)	Vc	I <sub>PP</sub> =2A			75	V
Peak Pulse Current (tp=8/20µs)	I <sub>PP</sub>				3	Α
Off state junction capacitance	CJ	0Vdc,f=1MHz		0.8		pF

### **Typical Characteristics Curves**

Figure 1. Power Derating Curve

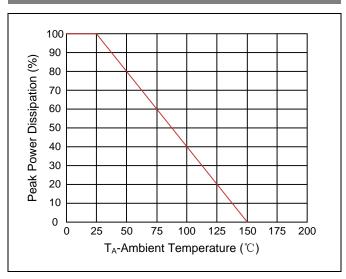


Figure 2. Pulse Waveform

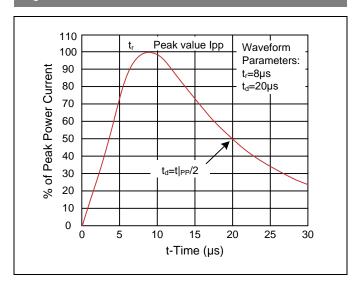


Figure 3. Non-Repetitive Peak Pulse vs Pulse Time

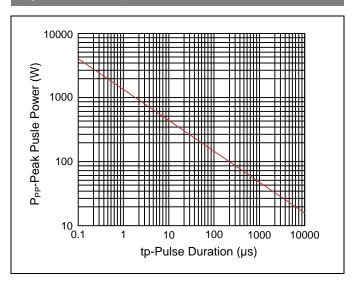
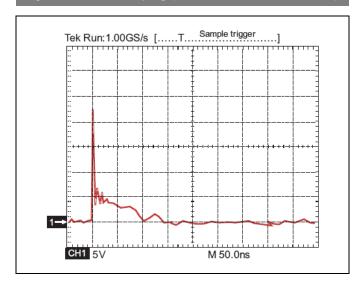
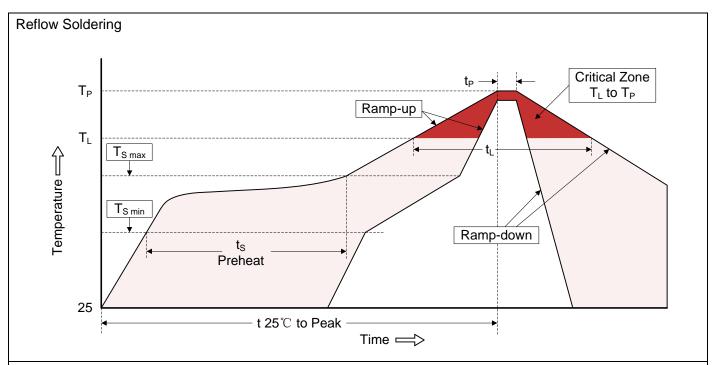


Figure 4. ESD Clamping (8kV Contact IEC61000-4-2)



### **Recommended Soldering Conditions**

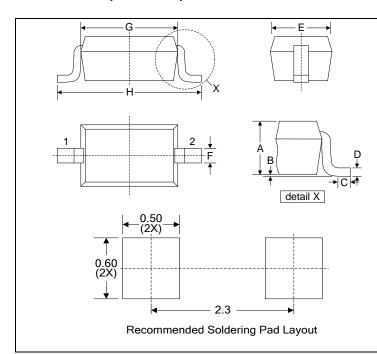


### **Recommended Condition**

Profile Feature	Pb-Free Assembly
Average ramp-up rate (T <sub>L</sub> to T <sub>P</sub> )	3°C/second max.
Preheat -Temperature Min (T <sub>S min</sub> ) -Temperature Max (T <sub>S max</sub> ) -Time (min to max) (ts)	150°C 200°C 60-180 seconds
T <sub>S max</sub> to T <sub>L</sub> -Ramp-up Rate	3°C/second max.
Time maintained above: -Temperature (T <sub>L</sub> ) -Time (t <sub>L</sub> )	217°C 60-150 seconds
Peak Temperature (T <sub>P</sub> )	260°C
Time within 5°C of actual Peak Temperature (t <sub>P</sub> )	20-40 seconds
Ramp-down Rate	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

### Electrostatic Discharge Protection Devices | UDD32CXXL01

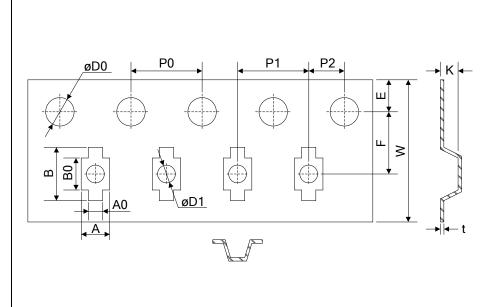
### **Dimensions (SOD-323)**



	Dimension					
Symbol	Millim	neters	Inches			
	Min.	Max.	Min.	Max.		
Α	0.80	1.10	0.031	0.043		
В	0.00	0.10	0.000	0.004		
С	0.20	-	0.008	-		
D	0.11	0.20	0.004	0.008		
E	1.15	1.35	0.045	0.053		
F	0.25	0.35	0.010	0.014		
G	1.60	1.80	0.063	0.071		
Н	2.40	2.70	0.094	0.102		

### **Packaging**

Tape



Symbol	Dimension (mm)		
W	8.00±0.30		
P0	4.00±0.10		
P1	4.00±0.10		
P2	2.00±0.10		
D0	Ф1.55±0.10		
D1	Ф1.00±0.05		
Е	1.75±0.10		
F	3.50±0.10		
Α	1.48±0.10		
A0	0.80±0.10		
В	3.00±0.10		
В0	1.80±0.10		
K	1.05±0.10		
t	0.25±0.05		
D	Ф178.0±2.0		
D2	Ф13.0		
W1	9.5		
Quantity: 3000PCS			

Reel

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### YAGEO:

UDD32C12L01 UDD32C05L01 UDD32C03L01 UDD32C15L01 UDD32C24L01 UDD32C08L01